Amended Claims

1. (withdrawn) A LVTSCR-like structure having one or more diodes formed in a p-well of the structure.

2. (currently amended) A method of increasing the holding voltage of an LVTSCR structure that includes an n-well and a p-well formed in a substrate, ~~an~~ a first n+ region and a first p+ region formed in the n-well to define a high voltage node and ~~an~~ a second n+ region and a second p+ region formed in the p-well to define a low voltage node, the method comprising forming at least one additional p+ region and at least one additional n+ region inside the p-well of the structure to define at least one p-n junction between the p-type material ~~of~~ as defined by the p-well and one of the additional p+ regions in the p-well on the one hand, and the n-type material of one of the additional n+ regions in the p-well on the other hand, the p-n junction being forward biased during normal operation by having said additional p+ region of the p-n junction located closer to the high voltage node than the additional n+ region of the p-n junction.

3. (previously presented) A method of increasing the holding voltage of an LVTSCR structure having an anode in an n-well and a cathode in a p-well, the cathode being defined by an n+ region and a p+ region, comprising

forming at least one additional n+ region and at least one additional p+ region in the p-well to define at least one forward biased diode under normal operation in the p-well, thereby providing an alternative current path from anode to cathode through said at least one diode.

4. (original) A method of claim 3, wherein the alternative current path defines a lower resistance current path than the p-well.

5. (canceled)

6. (canceled)

7. (canceled)

8. (canceled)